



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	Toshiharu Furukawa et al.	:	Date: January 28, 2004
Group Art Unit:	Unassigned	:	IBM Corporation
Examiner:	Unassigned	:	Intellectual Property Law
Serial No.:	10/732,951	:	Dept. 917, Bldg. 006-1
Filed:	December 11, 2003	:	3605 Highway 52 North
Title:	SELECTIVE SYNTHESIS OF SEMICONDUCTING CARBON NANOTUBES	:	Rochester, MN 55901-7829

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Applicants request that the information listed on the attached Form PTO/SB/08A be considered by the Office during the pendency of the above entitled application, pursuant to 37 C.F.R. §1.97. In accordance with 37 C.F.R. §1.97(h), the filing of this Information Disclosure Statement shall not constitute an admission that any information cited therein is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b). In the interest of full and complete disclosure to the Office, some or all of the art cited herein may not be considered by Applicant(s) or the Undersigned to be material under the new standard of materiality defined in 37 C.F.R. §1.56(b), enacted March 16, 1992, but may be material under the old standard of materiality defined in 37 C.F.R. §1.56(a), last amended on November 28, 1988, or may merely be technical background which may be of interest to the Examiner. In accordance with

Serial No. 10/732,951
Docket No. ROC920030269US1

PATENT

37 C.F.R. §1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made.

This Information Disclosure Statement is being filed under 37 C.F.R. §1.97(b)(1) within three months of the filing date of the present application. Accordingly no filing fee is required.

Date: January 28, 2004

Respectfully submitted,

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Debra A. Peterson
Debra A. Peterson

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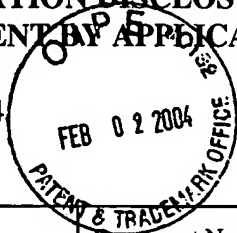
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Sheet 1 of 4



Application Number.: 10/732,951
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 First Named Inventor: Toshiharu Furukawa
 Art Unit: Unassigned
 Examiner Name: Unassigned
 Attorney Docket Number.: ROC920030269US1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns or Lines Where Relevant Passages or Figs. Appear
		Number - Kind Code ² (if known)			
		US - 6,423,583 B1	07-23-2002	Avouris et al.	
		US - 6,515,325 B1	02-04-2003	Farnworth et al.	
		US - 2003/0168683 A1	09-11-2003	Farnworth et al.	
		US - 2003/0170930 A1	09-11-2003	Choi et al.	
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FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns or Lines Where Relevant Passages or Figs. Appear	T ⁶
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⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language translation is attached.

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and or country where published.	T ²
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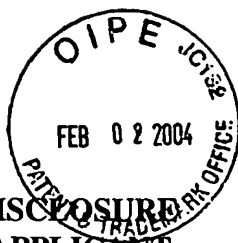
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 Examiner Name: Unassigned
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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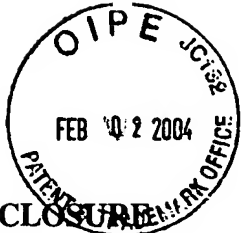
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